

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China



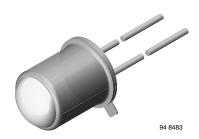




Vishay Semiconductors



Infrared Emitting Diode, RoHS Compliant, 875 nm, GaAlAs



DESCRIPTION

TSTA7100 is an infrared, 875 nm emitting diode in GaAlAs technology in a hermetically sealed TO-18 package with lens.

FEATURES

Package type: leaded
Package form: TO-18
Dimensions (in mm): Ø 4.7
Peak wavelength: λ_p = 875 nm

High reliability

· High radiant power

· High radiant intensity

• Angle of half intensity: ϕ = ± 5°

• Low forward voltage

• Suitable for high pulse current operation

· Good spectral matching with Si photodetectors

 Lead (Pb)-free component in accordance with RoHS 2002/95/EC and WEEE 2002/96/EC



· Radiation source near infrared range

PRODUCT SUMMARY					
COMPONENT	I _e (mW/sr)	φ (deg)	λ _P (nm)	t _r (ns)	
TSTA7100	50	± 5	875	600	

Note

Test conditions see table "Basic Characteristics"

ORDERING INFORMATION					
ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM		
TSTA7100	Bulk	MOQ: 1000 pcs, 1000 pcs/bulk	TO-18		

Note

MOQ: minimum order quantity

ABSOLUTE MAXIMUM RATINGS					
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT	
Reverse voltage		V _R	5	V	
Forward current		I _F	100	mA	
Peak forward current	$t_p/T = 0.5, t_p \le 100 \ \mu s$	I _{FM}	200	mA	
Surge forward current	t _p ≤ 100 μs	I _{FSM}	2.5	Α	
Dower discination		P _V	180	mW	
Power dissipation	T _{case} ≤ 25 °C	P _V	500	mW	
Junction temperature		Tj	100	°C	
Storage temperature range		T _{stg}	- 55 to + 100	°C	
Thermal resistance junction/ambient	leads not soldered	R _{thJA}	450	K/W	
Thermal resistance junction/case	leads not soldered	R _{thJC}	150	K/W	

Note

T_{amb} = 25 °C, unless otherwise specified

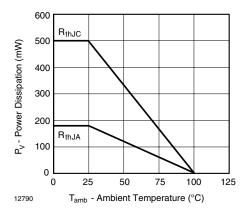




RoHS



Infrared Emitting Diode, RoHS Compliant, Vishay Semiconductors 875 nm, GaAlAs





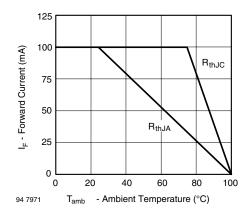


Fig. 2 - Forward Current Limit vs. Ambient Temperature

BASIC CHARACTERISTICS						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Forward voltage	$I_F = 100 \text{ mA}, t_p \le 20 \text{ ms}$	V_{F}		1.4	1.8	٧
Breakdown voltage	I _R = 100 μA	V _(BR)	5			٧
Junction capacitance	V _R = 0 V, f = 1 MHz, E = 0	Cj		20		pF
Radiant intensity	$I_F = 100 \text{ mA}, t_p \le 20 \text{ ms}$	l _e	20	50	100	mW/sr
Radiant power	$I_F = 100 \text{ mA}, t_p \le 20 \text{ ms}$	фe		10		mW
Temperature coefficient of ϕ_e	I _F = 100 mA	TKφ _e		- 0.7		%/K
Angle of half intensity		φ		± 5		deg
Peak wavelength	I _F = 100 mA	λ_{p}		875		nm
Spectral bandwidth	I _F = 100 mA	Δλ		80		nm
Rise time	I _F = 100 mA	t _r		600		ns
	$I_F = 1.5 \text{ A}, t_p/T = 0.01, t_p \le 10 \mu\text{s}$	t _r		300		ns
Virtual source diameter		d		1.5		mm

Note

 T_{amb} = 25 °C, unless otherwise specified

BASIC CHARACTERISTICS

 T_{amb} = 25 °C, unless otherwise specified

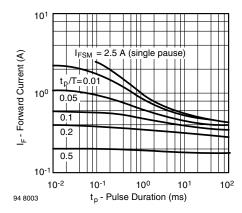


Fig. 3 - Pulse Forward Current vs. Pulse Duration

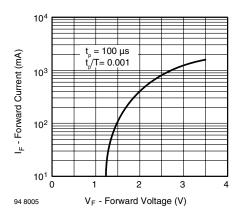


Fig. 4 - Forward Current vs. Forward Voltage

Vishay Semiconductors Infrared Emitting Diode, RoHS Compliant, 875 nm, GaAlAs



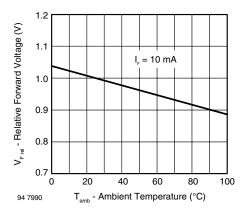


Fig. 5 - Relative Forward Voltage vs. Ambient Temperature

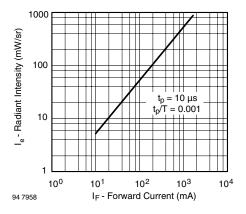


Fig. 6 - Radiant Intensity vs. Forward Current

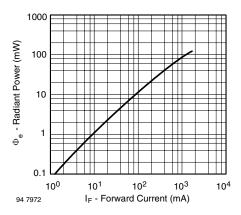


Fig. 7 - Radiant Power vs. Forward Current

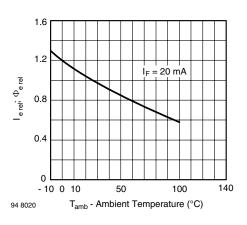


Fig. 8 - Rel. Radiant Intensity/Power vs. Ambient Temperature

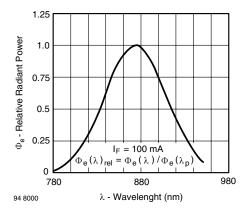


Fig. 9 - Relative Radiant Power vs. Wavelength

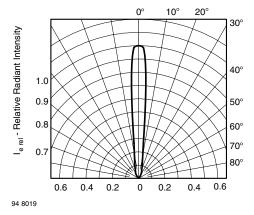
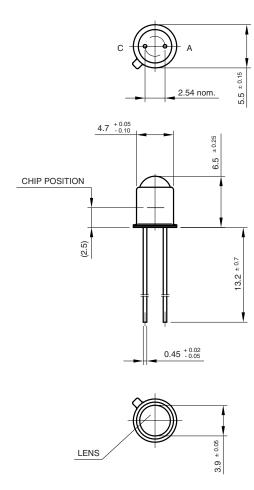


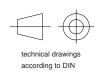
Fig. 10 - Relative Radiant Intensity vs. Angular Displacement



Infrared Emitting Diode, RoHS Compliant, Vishay Semiconductors 875 nm, GaAlAs

PACKAGE DIMENSIONS in millimeters





specifications

Drawing-No.: 6.503-5002.01-4

Issue: 2; 24.08.98

96 12174



Legal Disclaimer Notice

Vishay

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.